# **NDBA100N10B**

# **Power MOSFET** 100V, 6.9mΩ, 100A, N-Channel

#### **Features**

- Low On-Resistance
- Low Gate Charge
- High Speed Switching
- 100% Avalanche Tested
- Pb-Free, Halogen Free and RoHS Compliance

#### **Specifications**

#### Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Value	Unit
Drain to Source Voltage	VDSS	100	V
Gate to Source Voltage	V <sub>GSS</sub>	±20	V
Drain Current (DC)	ID	100	А
Drain Current (Pulse) PW≤10μs, duty cycle≤1%	I <sub>DP</sub>	400	A
Power Dissipation Tc=25°C	PD	110	W
Junction Temperature	Tj	175	°C
Storage Temperature	Tstg	-55 to +175	°C
Source Current (Body Diode)	IS	100	А
Avalanche Energy (Single Pulse) *1	E <sub>AS</sub>	147	mJ
Lead Temperature for Soldering Purposes, 3mm from Case for 10 Seconds	TL	260	°C

#### **Thermal Resistance Ratings**

Parameter	Symbol	Value	Unit	
Junction to Case Steady State	R <sub>0JC</sub>	1.36	0000	
Junction to Ambient *2	R <sub>0JA</sub>	62.5	°C/W	

Note : \*1 VDD=48V, L=100µH, IAV=40A (Fig.1)

\*2 Surface mounted on FR4 board using recommended footprint

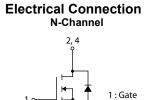
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

#### **ORDERING INFORMATION**

See detailed ordering and shipping information on page 5 of this data sheet.



Veee	Ppo(on) Moy	
VDSS	R <sub>DS</sub> (on) Max	ID Max
100V	6.9 mΩ@15V	
	8.2 mΩ@10V	100A



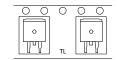








#### Packing Type : TL

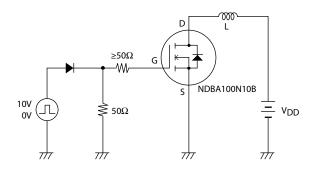


#### **Electrical Characteristics** at $Ta = 25^{\circ}C$

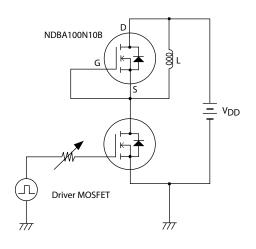
Parameter	O: make al	Quality and	Value			
	Symbol	Conditions	min	typ	max	Unit
Drain to Source Breakdown Voltage	V(BR)DSS	I <sub>D</sub> =10mA, V <sub>GS</sub> =0V	100			V
Zero-Gate Voltage Drain Current	IDSS	V <sub>DS</sub> =100V, V <sub>GS</sub> =0V			10	μA
Gate to Source Leakage Current	IGSS	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V			±100	nA
Gate Threshold Voltage	V <sub>GS</sub> (th)	V <sub>DS</sub> =10V, I <sub>D</sub> =1mA	2		4	V
Forward Transconductance	9FS	V <sub>DS</sub> =10V, I <sub>D</sub> =50A		75		S
Static Drain to Source On-State Resistance	R <sub>DS</sub> (on)1	I <sub>D</sub> =50A, V <sub>GS</sub> =15V		5.7	6.9	mΩ
	R <sub>DS</sub> (on)2	I <sub>D</sub> =50A, V <sub>GS</sub> =10V		6.3	8.2	mΩ
Input Capacitance	Ciss			2,950		pF
Output Capacitance	Coss	V <sub>DS</sub> =50V, f=1MHz		1,250		pF
Reverse Transfer Capacitance	Crss			20		pF
Turn-ON Delay Time	t <sub>d</sub> (on)			40		ns
Rise Time	tr			385		ns
Turn-OFF Delay Time	t <sub>d</sub> (off)	See Fig.2		68		ns
Fall Time	tf			52		ns
Total Gate Charge	Qg			35		nC
Gate to Source Charge	Qgs	V <sub>DS</sub> =48V, V <sub>GS</sub> =10V, I <sub>D</sub> =100A		13		nC
Gate to Drain "Miller" Charge	Qgd			10		nC
Forward Diode Voltage	V <sub>SD</sub>	I <sub>S</sub> =100A, V <sub>GS</sub> =0V		1.1	1.5	V
Reverse Recovery Time	trr	See Fig.3		130		ns
Reverse Recovery Charge	Q <sub>rr</sub>	I <sub>S</sub> =100A, V <sub>GS</sub> =0V, V <sub>DD</sub> =50V, di/dt=100A/μs		400		nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

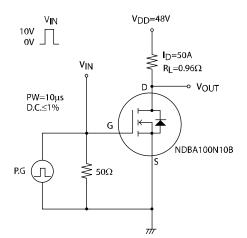
#### Fig.1 Unclamped Inductive Switching Test Circuit



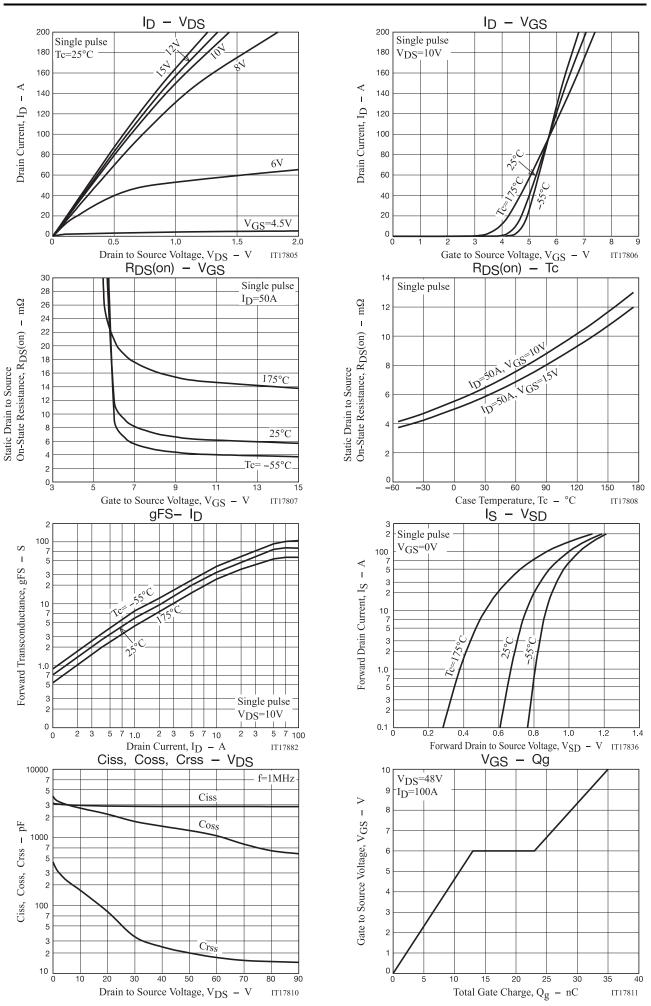
#### Fig.3 Reverse Recovery Time Test Circuit



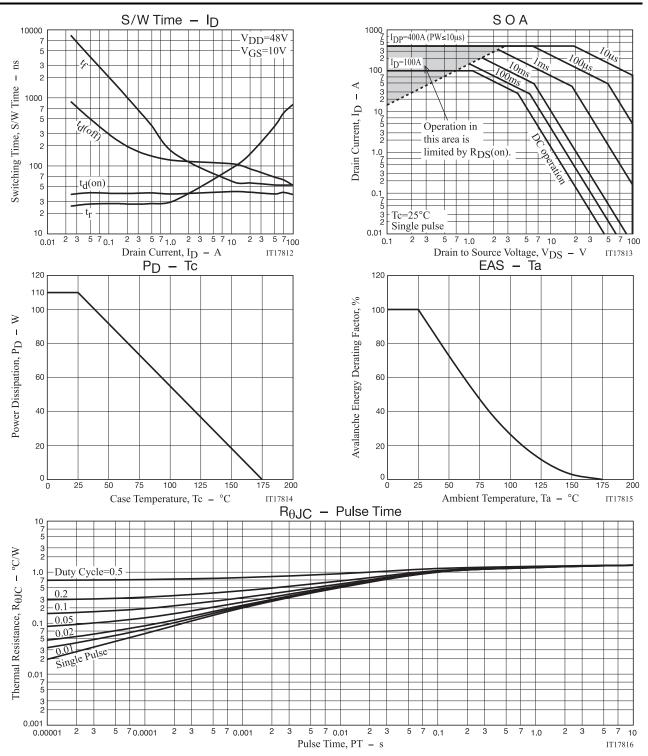
#### Fig.2 Switching Time Test Circuit



#### NDBA100N10B

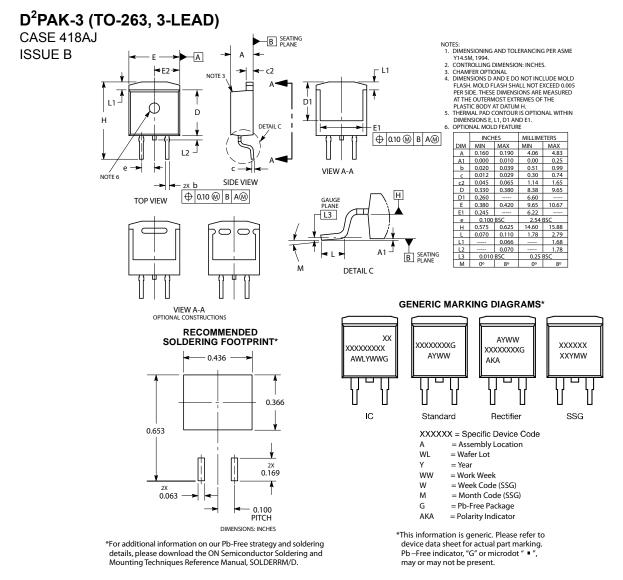


www.onsemi.com 3



#### Package Dimensions

NDBA100N10BT4H



#### **ORDERING INFORMATION**

Device	Package Shipping		note
NDBA100N10BT4H	D <sup>2</sup> PAK-3 (TO-263, 3-LEAD)	800 pcs. / Tape & Reel	Pb-Free and Halogen Free

† For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D. http://www.onsemi.com/pub\_link/Collateral/BRD8011-D.PDF

## Note on usage : Since the NDBA100N10B is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

ON Semiconductor and the ON logo are registered trademarks of Semiconductor Components Industries, LLC (SCILLC) or its subsidiaries in the United States and/or other countries. SCILLC owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of SCILLC's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILC was negligent regarding the design or

### **X-ON Electronics**

Largest Supplier of Electrical and Electronic Components

Click to view similar products for MOSFET category:

Click to view products by ON Semiconductor manufacturer:

Other Similar products are found below :

614233C 648584F IRFD120 JANTX2N5237 FCA20N60\_F109 FDZ595PZ 2SK2545(Q,T) 405094E 423220D TPCC8103,L1Q(CM MIC4420CM-TR VN1206L SBVS138LT1G 614234A 715780A NTNS3166NZT5G SSM6J414TU,LF(T 751625C BUK954R8-60E NTE6400 SQJ402EP-T1-GE3 2SK2614(TE16L1,Q) 2N7002KW-FAI DMN1017UCP3-7 EFC2J004NUZTDG ECH8691-TL-W FCAB21350L1 P85W28HP2F-7071 DMN1053UCP4-7 NTE221 NTE222 NTE2384 NTE2903 NTE2941 NTE2945 NTE2946 NTE2960 NTE2967 NTE2969 NTE2976 NTE455 NTE6400A NTE2910 NTE2916 NTE2956 NTE2911 DMN2080UCB4-7 TK10A80W,S4X(S SSM6P69NU,LF DMP22D4UF0-7B